Rev. 04/03

Docket No. ELM-1 Cont. 9

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Glenn J. Leedy

Application No.: 10/665,757 Confirmation No.: 6828

Filed : September 19, 2003

For : MEMBRANE IC FABRICATION

Group Art Unit : 2812

Examiner : Not yet assigned

New York, New York

July 2, 2004

Hon. Commissioner for Patents P.O. Box 1450 Alexandria, Virginia 22313-1450

TRANSMITTAL LETTER FOR INFORMATION DISCLOSURE STATEMENT

Sir:

Transmitted herewith is an Information Disclosure

Statement in the above-identified application. This

Statement is submitted:

- [] within three months of the application filing date;
- [X] more than three months from the application filing date but before the mailing date of the first Office Action on the merits.

In accordance with 37 C.F.R. § 1.97, submission of this Statement requires no fee. However, if for any reason a fee is due, the Director is hereby authorized to charge payment of any fees required in connection with this

Information Disclosure Statement to Deposit Account

No. 06-1075. A duplicate copy of this letter is transmitted herewith.

Respectfully submitted,

Philip R. Pol

Registration No. 51,176 Agent for Applicants

FISH & NEAVE

Customer No. 1473

1251 Avenue of the Americas

New York, New York 10020-1105

Tel.: (212) 596-9000

I hereby certify that this
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P.O. Box 1450

Claire J. Saintil-yan Goodman

Alexandria, VA 22313,1450 on

Signature of Person Signing

ELM-1 Cont.9

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants : Glenn J. Leedy

Application No.: 10/665,757 Confirmation No.: 6828

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Hon. Commissioner for Patents

P.O. Box 1450

Alexandrian, Virginia 22313-1450

INFORMATION DISCLOSURE STATEMENT

Sir:

In accordance with 37 C.F.R. §§ 1.56 and 1.97, applicant wishes to call the attention of the Examiner to the following documents:

U.S. Patents

Fujii et al.	Re. 34,893	04/04/95
Foster	2,915,722	12/01/59
Farrand	3,202,948	08/24/65
Lesk	3,559,282	02/02/71
Burkhardt	3,560,364	02/02/71
Emmasingel	3,602,982	09/07/71
Medicus	3,615,901	10/26/71
Napoli et al.	3,716,429	02/13/73
Krishna et al.	3,777,227	12/14/73
Kuipers	3,868,565	02/25/75
Yerman	3,922,705	11/25/75
Wanlass	3,997,381	12/14/76
Stein	4,070,230	01/24/78

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Greenwood et al.	4,131,985	01/02/79
Hauser, Jr., et al.	4,142,004	02/27/79
Hoeberechts	4,251,909	02/24/81
Kubacki	4,262,631	04/21/81
Shioya et al.	4,394,401	07/19/83
Trenkler et al.	4,401,986	08/30/83
Thomas et al.	4,416,054	11/22/83
Takagi et al.	4,539,068	09/03/85
Reid et al.	4,585,991	04/29/86
Yasumoto et al.	4,612,083	09/16/86
Belanger et al.	4,617,160	10/14/86
Shimizu et al.	4,618,397	10/21/86
Schmitz	4,618,763	10/21/86
Christensen	4,663,559	05/05/87
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Burns et al.	4,684,436	08/04/87
Hatada	4,693,770	09/15/87
Maeda et al.	4,702,336	10/27/87
Seibert et al.	4,702,936	10/27/87
Go	4,706,166	11/10/87
Stevenson	4,721,938	01/26/88
Reid	4,761,681	08/02/88
Holmen et al.	4,784,721	11/15/88
Freeman	4,810,673	03/07/89
Mattox et al.	4,825,277	04/25/89
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Leedy	4,924,589	05/15/90
Borel et al.	4,940,916	07/10/90
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Vranish et al.	4,950,987	08/21/90
Lee et al.	4,952,446	08/18/90
Rokos	4,954,865	09/04/90
Shinomiya	4,957,882	09/18/90
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Young et al.	4,965,415	10/23/90
Mauger	4,966,663	10/30/90
Leedy	4,994,735	02/19/91
Keogh et al.	5,008,619	04/16/91
Allen et al.	5,010,024	04/23/91
Leedy	5,020,219	06/04/91
Leedy	5,034,685	07/23/91
Greenwald et al.	5,070,026	12/03/91
Findler et al.	•	12/10/91
	5,071,510	
Machado et al.	5,098,865	03/24/92
Leedy	5,103,557	04/14/92
Mauger	5,110,373	05/05/92
Eichelberger	5,111,278	05/05/92
Chan et al.	5,116,777	05/26/92
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Dose	F 130 344	07/01/00
Roy	5,132,244	07/21/92
Hadwin	5,151,775	09/29/92
Henager, Jr., et al	5,156,909	10/20/92
Zimmerman	5,203,731	04/20/93
Leedy	5,225,771	07/06/93
Bower et al.		•
	5,236,118	08/17/93
Bureau et al.	5,262,351	11/16/93
Bertin et al.	5,270,261	12/14/93
Sanders	5,273,940	12/28/93
Tuckerman	5,274,270	12/28/93
Chebi et al.	5,279,865	01/18/94
Nakanishi et al.	5,284,796	02/08/94
Leedy	5,323,035	06/21/94
Wojnarowski	5,324,687	06/28/94
-		
Leedy	5,354,695	10/11/94
MacDonald	5,363,021	11/08/94
Goossen	5,385,632	01/31/95
Nelson et al.	5,385,909	10/25/94
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Miyake	5,424,920	06/13/95
Finnila	5,426,072	06/20/95
Akagi et al.	5,426,363	06/20/95
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	5,432,444	07/11/95
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Naruse	5,476,813	12/19/95
Gates	5,489,554	02/06/96
Bertin et al.	5,502,667	03/26/96
Leedy	5,512,397	04/30/96
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Pati et al.	5,527,645	06/18/96
Koskenmaki et al.	5,529,829	06/25/96
Frye et al.	5,534,465	07/09/96
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Leedy	5,654,127	08/05/97
Leedy	5,654,220	08/05/97
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Chen et al.	5,675,185	10/07/97
Ohara et al.	5,694,588	12/02/97
Leedy	5,725,995	03/10/98
Weise et al.	5,750,211	05/12/98
Bozso et al.	5,760,478	06/02/98
Okonogi	5,773,152	06/30/98
Rolfson	5,786,116	07/28/98
Zavracky et al.	5,793,115	08/11/98
Ray	5,831,280	11/03/98
Leedy	5,834,334	11/10/98
Leedy	5,840,593	11/24/98
Ito et al.	5,856,695	01/05/99
Sotokawa et al.	5,868,949	02/09/99
Leedy	5,869,354	02/09/99
Sweatt et al.	5,870,176	02/09/99
Davidson	5,880,010	03/09/99
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Hübner	5,902,118	05/11/99
Leedy	5,915,167	06/22/99
Leedy	5,946,559	08/31/99
Leedy	5,985,693	11/16/99
Cutter et al.	5,998,069	12/07/99
Leedy	6,008,126	12/28/99
Leedy	6,020,257	02/01/00
Houston	6,045,625	04/04/00
Adamic, Jr.	6,084,284	07/04/00
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Leedy	6,133,640	10/17/00
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Aleshin et al.	6,197,456 B1	03/06/01
Leedy	6,208,545 B1	03/00/01
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Lin	6,261,728 B1	03/22/01
Leedy	6,288,561 B1	09/11/01
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Lecuy	0,294,303 DI	09/11/01

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JAPAN	JP 04-083371	03/1992
JAPAN	JP 04-107964	04/1992
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Alloert, K., et al., "A Comparison Between Silicon Nitride Films Made by PCVD of N_2 -SiH₄ /A_r and N_2 -SiH₄/He," Journal of the Electrochemical Society, Vol. 132, No. 7, pp. 1763-1766, (July 1985).

Hendricks, et al., "Polyquinoline Coatings and Films: Improved Organic Dielectrics for IC's and MCM's," Eleventh IEEE/CHMT International Electronics Manufacturing Technology Symposium, "pp. 361-265 (1991).

Knolle, W.R., et al., "Characterization of Oxygen-Doped, Plasma-Deposited Silicon Nitride," Journal of the Electrochemical Society, Vol. 135, No. 5, pp. 1211-1217, (May 1988).

Nguyen, S.V., "Plasma Assisted Chemical Vapor Deposited Thin Films for Microelectronic Applications, J. Vac. Sci. Technol. Vol. B4, No. 5, pp.1159-1167, (Sep/Oct. 1986).

Olmer, et al., "Intermetal Dielectric Deposition by Plasma Enhanced Chemical Vapor Deposition," Fifth IEEE/CHMT International Electronic Manufacturing Technology Symposium - Design-to-Manufacturing Transfer Cycle," pp. 98-99 (1988).

Runyan, W.R., "Deposition of Inorganic Thin Films," Semiconductor Integrated Circuit Processing Technology, p. 142 (1990).

Sze, S.M., "Surface Micromachining," Semiconductor Sensors, pp. 58-63 (1994).

Vossen, John L., "Plasma-Enhanced Chemical Vapor Deposition," Thin Film Processes II, pp. 536-541 (1991).

Wolf, Stanley, "Basic of Thin Films," Silicon Processing for the VLSI Era, pp. 115, 192-193 and 199 (1986).

Copies of the aforementioned documents are listed on the accompanying Form PTO-1449 (submitted in duplicate).

It is respectfully requested that these documents be: (1) fully considered by the Patent and Trademark Office during the examination of this application; and (2) printed on any patent which may issue on this application. Applicant requests that a copy of Form PTO-1449, as considered and initialized by the Examiner, be returned with the next communication.

Consideration of the foregoing in relation to this patent application is respectfully requested.

Respectfully submitted,

THE MERCHANIS Continuor trains in high

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Cleas Mail in an outdope Addressed to:

Commission - for Potents

P.O. Box 1480

Alexandria, VA 22313-1450 on

Signature of Person Signing

Philip R. Roh

Registration No. 51,176

Agent for Applicant

FISH & NEAVE

Customer No. 1473

1251 Avenue of the Americas New York, New York 10020-1104

Tel.: (212) 596-9000

FORM PTO-1449

U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

ATTY. DOCKET NO. ELM-1 Cont. 9	APPLICATION NO. 10/665,757
APPLICANT Glenn J. Leedy	CONFIRMATION NO. 6828
FILING DATE September 19, 2003	GROUP 2812

U.S. PATENT DOCUMENTS

EXAMINE R INITIAL	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
	Re. 34,893	04/04/95	Fujii et al.	257	419	ALTROPRIATE
	2,915,722	12/01/59	Foster	336	115	
	3,202,948	08/24/65	Farrand	336	115	
	3,559,282	02/02/71	Lesk	438	113	
	3,560,364	02/02/71	Burkhardt	324	207.12	·
	3,602,982	09/07/71	Emmasingel	29	577	
	3,615,901	10/26/71	Medicus	148	11.5 R	
	3,716,429	02/13/73	Napoli et al.	156	17	
	3,777,227	12/14/73	Krishna et al.	257	578	
	3,868,565	02/25/75	Kuipers	324	207.26	
	3,922,705	11/25/75	Yerman	357	26	
	3,997,381	12/14/76	Wanlass	156	3	
_	4,070,230	01/24/78	Stein	156	657	
	4,131,985	01/02/79	Greenwood et al.	29	580	
	4,142,004	02/27/79	Hauser, Jr. et al.	438	792	
	4,251,909	02/24/81	Hoeberechts	29	580	
	4,262,631	04/21/81	Kubacki	118	723MP	
	4,394,401	07/19/83	Shioya et al.	427	574	-
	4,401,986	08/30/83	Trenkler et al.	340	870.32	
	4,416,054	11/22/83	Thomas et al.	29	572	
	4,539,068	09/03/85	Takagi et al.	156	614	
	4,585,991	04/29/86	Reid et al.	324	158 P	
	4,612,083	09/16/86	Yasumoto et al.	156	633	
	4,617,160	10/14/86	Belanger et al.	264	40.1	
	4,618,397	10/21/86	Shimizu et al.	156	628	
	4,618,763	10/21/86	Schmitz	250	211R	
	4,663,559	05/05/87	Christensen	313	336	
	4,684,436	08/04/87	Burns et al.	216	65	
	4,693,770	09/15/87	Hatada	156	151	

EXAMINER

FORM PTO-1449			OF COMMERCE EMARK OFFICE	ATTY. DOCI		APPLICATION NO. 10/665,757
	FORMATION DIS		· ·	APPLICANT Glenn J. Lee		CONFIRMATION NO. 6828
<u> </u>	TATEMENT BY A		ANI	FILING DAT September 1		GROUP 2812
4,702,	336 10/2	7/87	Maeda et al.	180	197	
4,702,		7/87	Seibert et al.	427	583	
4,706,		0/87	Go	361	403	
4,721,		6/88	Stevenson	338	4	
4,761,		2/88	Reid	357	68	
4,784,		5/88	Holmen et al.	156	647	
4,810,	· ·	7/89	Freeman	438	386	
4,825,		5/89	Mattox et al.	257	639	
4,857,		5/89	Tam et al.	438	619	
4,924,		5/90	Leedy	438	6	
4,940,	1	0/90	Borel et al.	313	306	
		6/96	Borel et al.	315	306	
4,950,	·	1/90	Vranish et al.	324	207.23	
4,952,		8/90	Lee et al.	428	220	
4,954,	1	4/90	Rokos	257	378	
4,957,		8/90	Shinomiya	438	65	
4,965,		3/90	Young et al.	200	83 N	
4,966,		0/90	Mauger	205	656	
4,994,		9/91	Leedy	324	158	
5,008,		6/91	Keogh et al.	324	207.17	
5,010,	024 04/2	3/91	Allen et al.	438	659	
5,020,	219 06/0	4/91	Leedy	29	846	
5,034,	685 07/2	3/91	Leedy	324	158 F	
5,070,	026 12/0	3/91	Greenwald et al.	437	3	
5,071,	510 12/1	0/91	Findler et al.	156	647	
5,098,	865 03/2	4/92	Machado et al.	438	788	
5,103,	557 04/1	4/92	Leedy	29	832	
5,110,	373 05/0	5/92	Mauger	148	33.2	
5,111,	278 05/0	5/92	Eichelberger	357	75	
5,116,	777 05/2	26/92	Chan et al.	438	234	
5,130,	894 07/1	4/92	Miller	361	393	
5,132,	244 07/2	21/92	Roy	438	477	

FORM PTO-1449		T OF COMMERCE ADEMARK OFFICE	ATTY. DOC ELM-1 Cont		APPLICATION NO. 10/665,757	
	FORMATION DISCLO		APPLICANT Glenn J. Le		CONFIRMATION NO 6828	
			FILING DAT September		GROUP 2812	
5,151,	775 09/29/92	Hadwin	357	80		
5,156,9		Henager, Jr. et al.	428	334		
5,203,		Zimmerman	445	24		
5,225,	771 07/06/93	Leedy	324	158		
5,236,	~	Bower et al.	228	193		
5,262,3	351 11/16/93	Bureau et al.	437	183		
5,270,		Bertin et al.	437	209		
5,273,		Sanders	437	209		
5,274,3	270 12/28/93	Tuckerman	257	758		
5,279,8	365 01/18/94	Chebi et al.	427	574		
5,284,	796 02/08/94	Nakanishi et al.	437	183		
5,323,0		Leedy	257	48		
5,324,0	687 06/28/94	Wojnarowski	437	225		
5,354,0		Leedy	438	411		
5,363,0	021 11/08/94	MacDonald	315	366		
5,385,0	632 01/31/95	Goossen	156	630		
5,385,9	909 01/31/95	Nelson et al.	514	291		
5,420,4	458 05/30/95	Shimoji	257	622		
5,424,9	920 06/13/95	Miyake	361	735		
5,426,0	072 06/20/95		437	208		
5,426,3	363 06/20/95	Akagi et al.	324	239		
5,432,4	144 07/11/95	Yasohama et al.	324	240		
5,432,	729 07/11/95	Carson et al.	365	63		
5,434,			324	67		
5,451,4	489 09/19/95	Leedy	430	313		
5,453,4	404 09/26/95		437	203		
5,457,			29	895		
5,476,	313 12/19/95	Naruse	437	132		
5,489,	554 02/06/96	Gates	437	208		
5,502,0		Bertin et al.	365	51		
5,512,	397 04/30/96	Leedy	430	30		
5,527,0		0	430	5		

FORM PTO-1449		T OF COMMERCE DEMARK OFFICE	ATTY. DOC ELM-1 Con		APPLICATION NO. 10/665,757
	FORMATION DISCLO		APPLICAN Glenn J. Le		CONFIRMATION NO 6828
	TATEMENT DI ALLE		FILING DA [*] September		GROUP 2812
5,529,	829 06/25/96	Koskenmaki et al.	428	167	T
5,534,	465 07/09/96	Frye et al.	437	209	
5,555,	212 09/10/96	Toshiaki et al.	365	200	
5,563,	084 10/08/96	Ramm et al.	437	51	
5,571,	741 11/05/96	Leedy	437	51	
5,580,	687 12/03/96	Leedy	430	5	
5,581,	498 12/03/96	Ludwig et al.	365	63	
5,582,		Pierrat	430	5	
5,583,	688 12/10/96	Hornbeck	359	291	
5,592,	007 01/07/97	Leedy	257	347	
5,592,	018 01/07/97	Leedy	257	619	
5,595,	933 01/21/97	Heijboer	439	20	
5,606,	186 02/25/97	Noda	257	226	
5,627,	112 05/06/97	Tennant et al.	438	113	
5,629,	137 05/13/97	Leedy	430	313	
5,633,	209 05/27/97	Leedy	435	228	
5,637,	536 06/10/97	Val	438	686	
5,654,	127 08/05/97	Leedy	430	315	
5,654,	220 08/05/97	Leedy	438	25	
5,656,	552 08/12/97	Hudak et al.	438	15	
5,675,	185 10/07/97	Chen et al.	257	774	
5,694,	588 12/02/97	Ohara et al.	395	566	
5,725,	995 03/10/98	Leedy	430	315	
5,750,	211 05/12/98	Weise et al.	427	579	
5,760,	478 06/02/98	Bozso et al.	257	777	
5,773,	152 06/30/98	Okonogi	428	446	
5,786,	116 07/28/98	Rolfson	430	5	
5,793,	115 08/11/98	Zavracky et al.	257	777	
5,831,	280 11/03/98	Ray	257	48	
5,834,	334 11/10/98	Leedy	438	107	
5,840,	593 11/24/98	Leedy	438	6	
5,856,	695 01/05/99	Ito et al.	257	370	

FORM PTO-1							I I			APPLICATION NO. 10/665,757		
	INFORMATIO		CLOSURE			1	APPLICANT Glenn J. Leedy			CONFIRMATION NO. 6828		
	STATEMENT	BY API	PLIC	ANT		· · · · · · · · · · · · · · · · · · ·			ROUP			
		- -										
	5,868,949	02/09/9	99	Sotokawa	 a et al.		216	18				
	5,869,354	02/09/9		Leedy			438	110				
	5,870,176	02/09/9		Sweatt e	t al.		355	53				
	5,880,010 03/09 5,882,532 03/16		99	Davidsor	1		438	455				
			$\overline{}$	Field et a			216	2				
	5,902,118	05/11/9		Hübner			438	106				
	5,915,167	06/22/9	99	Leedy			438	108			·	
	5,946,559	08/31/9		Leedy			438	157				
	5,985,693	11/16/					438	107				
	5,998,069	12/07/					430	5				
	6,008,126 12/28						438	667				
	6,020,257 02/01/0 6,045,625 04/04/0						438	626				
							148	33.3				
	6,084,284	07/04/	/00 Adamic, Jr.				257	506				
	6,097,096	08/01/					257	777				
	6,133,640	10/17/	10/17/00 Leedy 02/27/01 Tayanak		eedy Fayanaka Aleshin et al.		257 778					
	6,194,245 B1						438	57 5				
	6,197,456 B1						430					
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